

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/4622500/publications.pdf>

Version: 2024-02-01

115
papers

2,061
citations

304602

22
h-index

276775

41
g-index

117
all docs

117
docs citations

117
times ranked

2229
citing authors

#	ARTICLE	IF	CITATIONS
1	Nature of the Pt-Cobalt-Oxide surface interaction and its role in the CO ₂ Methanation. Applied Surface Science, 2022, 571, 151326.	3.1	23
2	Multiscale Investigation of the Structural, Electrical and Photoluminescence Properties of MoS ₂ Obtained by MoO ₃ Sulfurization. Nanomaterials, 2022, 12, 182.	1.9	15
3	Interfacial Ni active sites strike solid solution counterpart in CO ₂ hydrogenation. Environmental Technology and Innovation, 2022, 27, 102747.	3.0	9
4	Esaki Diode Behavior in Highly Uniform MoS ₂ /Silicon Carbide Heterojunctions. Advanced Materials Interfaces, 2022, 9, .	1.9	14
5	Controlling the morphology of poly(ethyleneimine)/gold nanoassemblies through the variation of pH and electrolyte additives. Journal of Molecular Liquids, 2021, 322, 114559.	2.3	7
6	Indium Nitride at the 2D Limit. Advanced Materials, 2021, 33, e2006660.	11.1	45
7	ZnSnN ₂ in Real Space and k-space: Lattice Constants, Dislocation Density, and Optical Band Gap. Advanced Optical Materials, 2021, 9, 2100015.	3.6	10
8	Material proposal for 2D indium oxide. Applied Surface Science, 2021, 548, 149275.	3.1	50
9	Structural Characteristics of the Si Whiskers Grown by Ni-Metal-Induced-Lateral-Crystallization. Nanomaterials, 2021, 11, 1878.	1.9	6
10	Highly Homogeneous Current Transport in Ultra-Thin Aluminum Nitride (AlN) Epitaxial Films on Gallium Nitride (GaN) Deposited by Plasma Enhanced Atomic Layer Deposition. Nanomaterials, 2021, 11, 3316.	1.9	6
11	A low temperature growth of Ca silicides on Si(100) and Si(111) substrates: Formation, structure, optical properties and energy band structure parameters. Journal of Alloys and Compounds, 2020, 813, 152101.	2.8	13
12	In situ TEM study of $\hat{1}\hat{0}\hat{1}^2$ and $\hat{1}\hat{0}\hat{1}^3$ phase transformations in Ga ₂ O ₃ . Acta Materialia, 2020, 183, 216-227.	3.8	60
13	Nanoscale phenomena ruling deposition and intercalation of AlN at the graphene/SiC interface. Nanoscale, 2020, 12, 19470-19476.	2.8	54
14	Diamond-Graphene Composite Nanostructures. Nano Letters, 2020, 20, 3611-3619.	4.5	54
15	Ambient pressure CO ₂ hydrogenation over a cobalt/manganese-oxide nanostructured interface: A combined in situ and ex situ study. Journal of Catalysis, 2020, 386, 70-80.	3.1	34
16	Temperature Dependent Vertical Conduction of GaN HEMT Structures on Silicon and Bulk GaN Substrates. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1800482.	0.8	5
17	Conductive CaSi ₂ transparent in the near infra-red range. Journal of Alloys and Compounds, 2019, 770, 710-720.	2.8	15
18	Effect of Added Surfactant on Poly(Ethyleneimine)-Assisted Gold Nanoparticle Formation. Langmuir, 2019, 35, 14007-14016.	1.6	7

#	ARTICLE	IF	CITATIONS
19	InGaN/(GaN)/AlGaIn/GaN normally-off metal-oxide-semiconductor high-electron mobility transistors with etched access region. Japanese Journal of Applied Physics, 2019, 58, SCCD21.	0.8	3
20	Structural and electrical properties of AlN thin films on GaN substrates grown by plasma enhanced-Atomic Layer Deposition. Materials Science in Semiconductor Processing, 2019, 97, 35-39.	1.9	11
21	Structural study of MgO and Mg-doped ZnO thin films grown by atomic layer deposition. Materials Science in Semiconductor Processing, 2019, 93, 6-11.	1.9	13
22	Barrier Inhomogeneity of Ni Schottky Contacts to Bulk GaN. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700613.	0.8	14
23	Formation of a Graphene-Like SiN Layer on the Surface Si(111). Semiconductors, 2018, 52, 1511-1517.	0.2	4
24	Low-Dispersion, High-Voltage, Low-Leakage GaN HEMTs on Native GaN Substrates. IEEE Transactions on Electron Devices, 2018, 65, 2939-2947.	1.6	36
25	The real structure of $\hat{\mu}$ -Ga ₂ O ₃ and its relation to $\hat{\nu}$ -phase. CrystEngComm, 2017, 19, 1509-1516.	1.3	227
26	Inclusions in Si whiskers grown by Ni metal induced lateral crystallization. Journal of Applied Physics, 2017, 121, .	1.1	10
27	Low-temperature atomic layer deposition-grown Al ₂ O ₃ gate dielectric for GaN/AlGaIn/GaN MOS HEMTs: Impact of deposition conditions on interface state density. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2017, 35, .	0.6	21
28	Preparation of Gold Nanocomposites with Tunable Charge and Hydrophobicity via the Application of Polymer/Surfactant Complexation. ACS Omega, 2017, 2, 8709-8716.	1.6	6
29	Index matching at the nanoscale: light scattering by core-shell Si/SiO _x nanowires. Nanotechnology, 2016, 27, 435202.	1.3	1
30	One-step green synthesis of gold nanoparticles by mesophilic filamentous fungi. Chemical Physics Letters, 2016, 645, 1-4.	1.2	52
31	Control of the in-plane thermal conductivity of ultra-thin nanocrystalline diamond films through the grain and grain boundary properties. Acta Materialia, 2016, 103, 141-152.	3.8	97
32	A Tool for Local Thickness Determination and Grain Boundary Characterization by CTEM and HRTEM Techniques. Microscopy and Microanalysis, 2015, 21, 422-435.	0.2	8
33	Novel Thermal Management of GaN Electronics: Diamond Substrates. , 2015, , .		5
34	Formation and thermoelectric properties of Si/CrSi ₂ /Si(001) heterostructures with stressed chromium disilicide nanocrystallites. Electronic Materials Letters, 2015, 11, 424-428.	1.0	5
35	Graphoepitaxy of High-Quality GaN Layers on Graphene/6H-SiC. Advanced Materials Interfaces, 2015, 2, 1400230.	1.9	23
36	Controlling the interface charge density in GaN-based metal-oxide-semiconductor heterostructures by plasma oxidation of metal layers. Journal of Applied Physics, 2015, 117, 214503.	1.1	3

#	ARTICLE	IF	CITATIONS
37	Thermal conductivity of ultrathin nano-crystalline diamond films determined by Raman thermography assisted by silicon nanowires. Applied Physics Letters, 2015, 106, .	1.5	40
38	Non-doped and doped Mg stannide films on Si(111) substrates: Formation, optical, and electrical properties. Japanese Journal of Applied Physics, 2015, 54, 07JC06.	0.8	5
39	Structure and Optical Properties of Ca Silicide Films and Si/Ca ₃ /Si ₄ /Si(111) Heterostructures. Solid State Phenomena, 2014, 213, 71-79.	0.3	5
40	Structural characteristics of single crystalline GaN films grown on (111) diamond with AlN buffer. Diamond and Related Materials, 2013, 34, 9-12.	1.8	6
41	Post-selenization of stacked precursor layers for CIGS. Vacuum, 2013, 92, 44-51.	1.6	22
42	Growth, structure, optical and electrical properties of Si/2D Mg ₂ /Si/Si(111) double heterostructures and Schottky diodes on their base. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1720-1723.	0.8	3
43	The Influence of C ₃ H ₈ and CBr ₄ on Structural and Morphological Properties of 3C-SiC Layers. Materials Science Forum, 2012, 711, 22-26.	0.3	0
44	TEM study of defects in Al _x Ga _{1-x} N layers with different polarity. Journal of Crystal Growth, 2012, 338, 30-34.	0.7	9
45	Growth of crack-free GaN epitaxial thin films on composite Si(111)/polycrystalline diamond substrates by MOVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 650-653.	0.8	1
46	Highly transparent ITO thin films on photosensitive glass: sol-gel synthesis, structure, morphology and optical properties. Applied Physics A: Materials Science and Processing, 2012, 107, 385-392.	1.1	15
47	Thin TaC layer produced by ion mixing. Surface and Coatings Technology, 2012, 206, 3917-3922.	2.2	7
48	Bilayer Cr/Au contacts on n-GaN. Vacuum, 2012, 86, 769-772.	1.6	1
49	Photoluminescence of samples produced by electroless wet chemical etching: Between silicon nanowires and porous structures. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 893-899.	0.8	14
50	Influence of CrSi ₂ nanocrystals on the electrical properties of Au/Si - p/CrSi ₂ NCs/Si(111) - n mesa-diodes. Physics Procedia, 2011, 11, 35-38.	1.2	1
51	Influence of Doping and Co-Doping on the Behavior of Sputtered ZnO Thin Films. ECS Transactions, 2011, 35, 141-148.	0.3	1
52	Electrical behaviour of lateral Al/n-GaN/Al structures. Applied Surface Science, 2010, 256, 5614-5617.	3.1	7
53	Migration of CrSi ₂ nanocrystals through nanopipes in the silicon cap. Applied Surface Science, 2010, 256, 7331-7334.	3.1	11
54	SiC Epitaxial Growth on Si(100) Substrates Using Carbon Tetrabromide. Materials Science Forum, 2010, 645-648, 139-142.	0.3	1

#	ARTICLE	IF	CITATIONS
55	Characterization of Plasma-Induced Damage of Selectively Recessed GaN/InAlN/AlN/GaN Heterostructures Using SiCl ₄ and SF ₆ . Japanese Journal of Applied Physics, 2010, 49, 116506.	0.8	11
56	Al and Ti/Al contacts on n-GaN. Vacuum, 2009, 84, 228-230.	1.6	9
57	Structural and electrical properties of Au and Ti/Au contacts to n-type GaN. Vacuum, 2008, 82, 794-798.	1.6	19
58	Si surface preparation and passivation by vapor phase of heavy water. , 2008, , .		0
59	Transmission electron microscopy of nanocomposite CrB ₄ -N thin films. Vacuum, 2007, 82, 209-213.	1.6	21
60	Surface Transformations and Growth of Nanocrystals on Au-covered GaAs Crystals. Nanopages, 2006, 1, 85-95.	0.2	3
61	Transmission electron microscope specimen preparation for exploring the buried interfaces in plan view. Journal of Microscopy, 2006, 224, 328-331.	0.8	4
62	Crystallization of amorphous-Si films by flash lamp annealing. Applied Surface Science, 2005, 242, 185-191.	3.1	77
63	Growth of highly curved Al _{1-x} In _x N nanocrystals. Physica Status Solidi (A) Applications and Materials Science, 2005, 202, R76-R78.	0.8	14
64	Isolated SiC nanocrystals in SiO ₂ . Applied Physics Letters, 2005, 86, 253109.	1.5	22
65	Optical and Structural Characteristics of Virtually Unstrained Bulk-Like GaN. Japanese Journal of Applied Physics, 2004, 43, 1264-1268.	0.8	37
66	Diamond formation by carbon implantation into cubic silicon carbide. Diamond and Related Materials, 2004, 13, 627-632.	1.8	5
67	Polarity dependent Al ₂ O ₃ /Ti contacts to 6H-SiC. Applied Surface Science, 2004, 233, 360-365.	3.1	24
68	TEM investigation of defect structure in GaAlN/GaN heterostructures. Vacuum, 2003, 71, 159-163.	1.6	2
69	Microstructure of GaN layers grown on Si(111) revealed by TEM. Vacuum, 2003, 71, 285-291.	1.6	14
70	Ti ₃ SiC ₂ formed in annealed Al/Ti contacts to p-type SiC. Applied Surface Science, 2003, 206, 8-11.	3.1	60
71	Transmission electron microscopy of wide band-gap semiconductor layers. Physica Status Solidi A, 2003, 195, 214-221.	1.7	2
72	Ion beam synthesis of diamond-SiC-heterostructures. Diamond and Related Materials, 2003, 12, 1241-1245.	1.8	7

#	ARTICLE	IF	CITATIONS
73	Structural Properties of Nickel-Metal-Induced Laterally Crystallized Silicon Films. Solid State Phenomena, 2003, 93, 213-218.	0.3	1
74	Microstructure of GaN Layers Grown onto (001) and (111) GaAs Substrates by Molecular Beam Epitaxy. Materials Science Forum, 2003, 433-436, 999-1002.	0.3	0
75	Structural Properties of Nickel Metal-Induced Laterally Crystallized Silicon Films and Their Improvement Using Excimer Laser Annealing. Japanese Journal of Applied Physics, 2003, 42, 2592-2599.	0.8	17
76	Diamond formation in cubic silicon carbide. Applied Physics Letters, 2003, 82, 46-48.	1.5	9
77	Void-Free Epitaxial Growth of Cubic SiC Crystallites during CO Heat Treatment of Oxidized Silicon. Materials Science Forum, 2002, 389-393, 359-362.	0.3	5
78	Catalytic Probe of the Surface Statistics of Palladium Crystallites Deposited on Montmorillonite. Chemistry of Materials, 2002, 14, 2882-2888.	3.2	57
79	Contact formation in SiC devices. Applied Surface Science, 2001, 184, 287-294.	3.1	49
80	TEM Investigation of Si Implanted Natural Diamond. Materials Science Forum, 2001, 353-356, 199-204.	0.3	4
81	Characterization of GaAlN/GaN Superlattice Heterostructures. Materials Science Forum, 2001, 353-356, 803-806.	0.3	2
82	High Dose Implantation in 6H-SiC. Materials Science Forum, 2001, 353-356, 579-582.	0.3	0
83	Ion-beam synthesis of epitaxial silicon carbide in nitrogen-implanted diamond. Applied Physics Letters, 2000, 77, 226-228.	1.5	15
84	Ion beam synthesis of graphite and diamond in silicon carbide. Applied Physics Letters, 2000, 76, 2847-2849.	1.5	19
85	Phase formation due to high dose aluminum implantation into silicon carbide. Journal of Applied Physics, 2000, 87, 78-85.	1.1	20
86	Consequences of High-Dose, High Temperature Al ⁺ Implantation in 6H-SiC. Materials Science Forum, 2000, 338-342, 881-884.	0.3	1
87	Formation of Precipitates in 6H-SiC after Oxygen Implantation and Subsequent Annealing. Materials Science Forum, 2000, 338-342, 961-964.	0.3	0
88	Epitaxial aluminum carbide formation in 6H-SiC by high-dose Al ⁺ implantation. Applied Physics Letters, 1999, 74, 2602-2604.	1.5	10
89	Electrical and structural characterisation of NiGe/n-GaAs interface. Vacuum, 1998, 50, 395-398.	1.6	0
90	Electrical and microstructure analysis of Ni/Ge/n-GaAs interface. Thin Solid Films, 1998, 323, 212-216.	0.8	1

#	ARTICLE	IF	CITATIONS
91	Amorphisation and surface morphology development at low-energy ion milling. Ultramicroscopy, 1998, 70, 161-171.	0.8	114
92	Physical and Electrical Characterization of W/N Schottky Contacts on 4H-SiC. Materials Science Forum, 1998, 264-268, 817-820.	0.3	5
93	Fast Generation-Recombination Channels due to Epitaxial Defects in SiC Metal-Oxide-Semiconductor Devices. Materials Science Forum, 1998, 264-268, 1025-1028.	0.3	8
94	Structural Characterisation of GaN Layers on Sapphire Grown by MOCVD. Materials Science Forum, 1998, 264-268, 1255-1258.	0.3	0
95	Topology of twin junctions in epitaxial $\hat{\Gamma}^2$ -SiC. Diamond and Related Materials, 1997, 6, 1362-1364.	1.8	7
96	TEM study of Ni and Ni ₂ Si ohmic contacts to SiC. Diamond and Related Materials, 1997, 6, 1428-1431.	1.8	38
97	The mechanism for cubic SiC formation on off-oriented substrates. Journal of Crystal Growth, 1997, 178, 495-504.	0.7	38
98	Tin dioxide sol-gel derived thin films deposited on porous silicon. Sensors and Actuators B: Chemical, 1997, 43, 114-120.	4.0	44
99	Early stages of growth of $\hat{\Gamma}^2$ -SiC on Si by MBE. Journal of Crystal Growth, 1995, 157, 392-399.	0.7	52
100	Growth and ellipsometric studies of periodic and cantor aperiodic amorphous Ge/Si superlattices. Thin Solid Films, 1994, 240, 7-13.	0.8	5
101	Reactive ion milling-thinning of compound semiconductors. Vacuum, 1994, 45, 1-3.	1.6	7
102	Structural and electrical properties of Ni films grown on Si(100) and SiO ₂ by d.c. bias sputtering. Thin Solid Films, 1993, 229, 107-112.	0.8	21
103	Crystallization of encapsulated very thin amorphous Ge layers. Thin Solid Films, 1993, 232, 68-72.	0.8	12
104	Ion mixing enhanced wafer bonding for silicon-insulator structures. Journal of Applied Physics, 1992, 72, 5602-5605.	1.1	0
105	Regrowth of a thin InP surface covering layer in the Au/InP system during annealing. Applied Physics Letters, 1992, 61, 105-107.	1.5	3
106	X-TEM investigation of the Al-QC layer system developed at various Mn deposition rates. Vacuum, 1992, 43, 673-675.	1.6	1
107	Simple method for the preparation of inp based samples for TEM investigation. Journal of Electron Microscopy Technique, 1991, 18, 325-328.	1.1	18
108	Electrophysical Parameters of the Metal-Semiconductor Interface in MBE and VPE Grown GaAs Schottky Contacts. Materials Science Forum, 1991, 69, 99-100.	0.3	0

#	ARTICLE	IF	CITATIONS
109	The influence of ohmic metal composition on the characteristics of ohmic contacts. <i>Vacuum</i> , 1990, 40, 179-181.	1.6	3
110	Thermal behaviour of Au/AlIIBV samples controlled with mass spectrometer. <i>Vacuum</i> , 1990, 40, 185-187.	1.6	2
111	The interaction of gold thin films with InP. <i>Vacuum</i> , 1990, 40, 189-191.	1.6	5
112	Interaction of thin gold films with GaP during heat treatment in a vacuum. <i>Semiconductor Science and Technology</i> , 1987, 2, 428-436.	1.0	5
113	Comparative mass spectrometric study of AlIII-BV compounds covered with a gold layer. <i>Vacuum</i> , 1986, 36, 547-549.	1.6	11
114	Structural Characterization of 3C-SiC Grown Using Methyltrichlorosilane. <i>Materials Science Forum</i> , 0, 740-742, 291-294.	0.3	1
115	Van der Waals and Graphene-Like Layers of Silicon Nitride and Aluminum Nitride. , 0, , .		5